

EAST Search History

10/540720

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	2	("6350703").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/09/17 09:29
L2	2	("4968636").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/09/17 09:29
L3	2	("6313014").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/09/17 09:29
L4	323	(438/311).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/09/17 09:30
L5	1429	(438/238).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/09/17 09:30
L6	2070	(438/197).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/09/17 09:30
L7	1349	(438/199).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/09/17 09:30
L8	55	(438/428).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/09/17 09:30

EAST Search History

L9	1870	(438/680).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/09/17 09:30
L10	961	(438/510).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/09/17 09:30
L11	180	(438/513).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/09/17 09:30
L12	1141	(438/723).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/09/17 09:31
L13	650	(438/724).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/09/17 09:31
L14	668	(438/756).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/09/17 09:31
L15	249	(438/757).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/09/17 09:31
L16	2	2 and (mask or ion or oxygen or impantaing or implantation or surface or major or silicon or oxide or nitride or protective or protection or single or crystal or substrate or heat or heating or treatment or annealing or anneal or quality)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/09/17 09:52

EAST Search History

L17	2	1 and (mask or ion or oxygen or impantaing or implantation or surface or major or silicon or oxide or nitride or protective or protection or single or crystal or substrate or heat or heating or treatment or annealing or anneal or quality)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/09/17 09:52
S86	1	10/540720	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/09/16 18:54
S87	2	("20020022348").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/09/16 18:55
S88	2	("20030104681").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/09/16 18:57
S89	2	("5930642").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/09/16 18:57
S90	2	("6593173").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/09/16 18:58
S91	4	single adj crystal adj silicon adj substate	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/09/16 19:01
S92	4	S91 and (mask or ion or oxygen or impantaing or implantation or surface or major or silicon or oxide or nitride or protective or protection or single or crystal or substrate or heat or heating or treatment or annealing or anneal or quality)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/09/17 09:31

EAST Search History

S93	261	(single adj crystal adj silicon) and mask and (oxygen adj ions) and (silicon adj oxide)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/09/16 19:20
S94	197	(single adj crystal adj silicon) and mask and (oxygen adj ions) and (silicon adj oxide) and substrate and (silicon adj nitride)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/09/16 19:21
S95	0	(single adj crystal adj silicon) and mask and (oxygen adj ions) and (silicon adj oxide) and substrate and (silicon adj nitride)and (heat adj treatment)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/09/16 19:21
S96	84	(single adj crystal adj silicon) and mask and (oxygen adj ions) and (silicon adj oxide) and substrate and (silicon adj nitride)and (heat adj treatment)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/09/16 19:21
S97	49	(single adj crystal adj silicon adj substrate) and mask and (oxygen adj ions) and (silicon adj oxide) and substrate and (silicon adj nitride)and (heat adj treatment)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/09/17 09:29